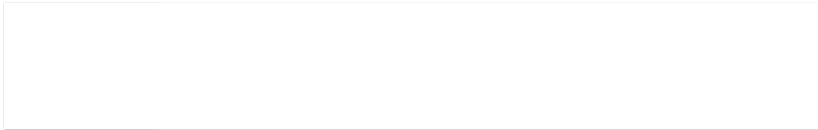


FRED

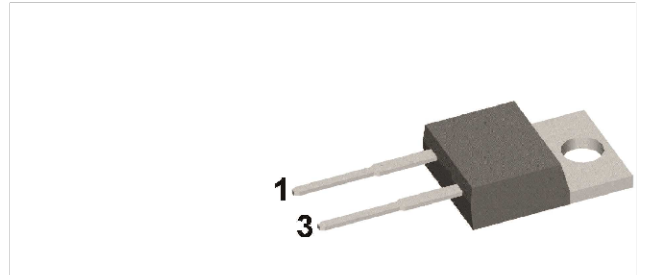


$V_{RRM} = 600\text{ V}$
 $I_{FAV} = 8\text{ A}$
 $t_{rr} = 35\text{ ns}$

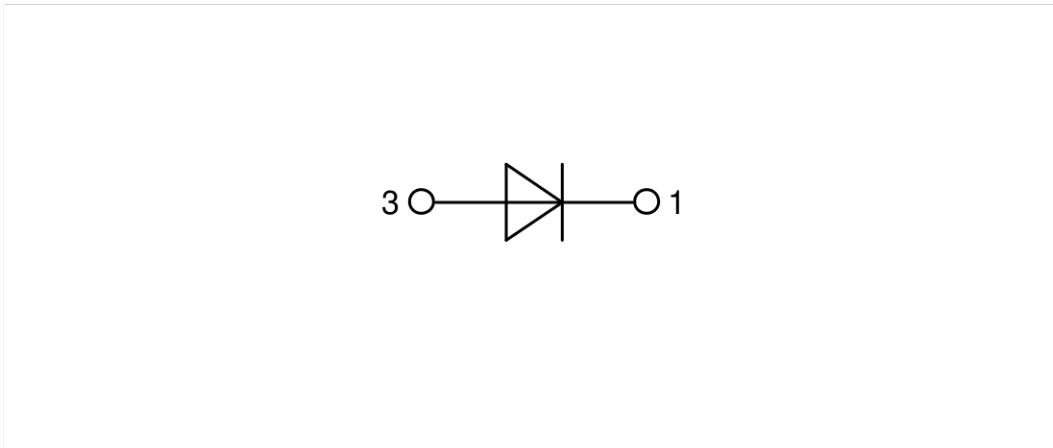
Fast Recovery Epitaxial Diode
Single Diode

Part number

DSEI8-06A



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

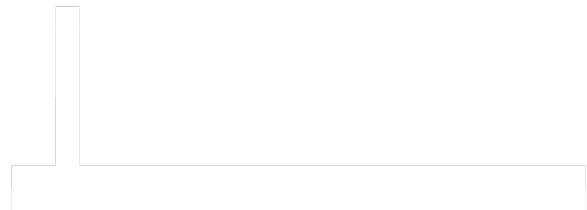
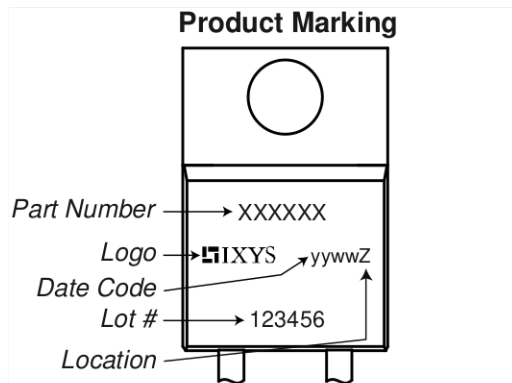
Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.



Fast Diode			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			600	V
I_R	reverse current, drain current	$V_R = 600 V$	$T_{VJ} = 25^{\circ}C$		20	μA
		$V_R = 480 V$	$T_{VJ} = 125^{\circ}C$		1.5	mA
V_F	forward voltage drop	$I_F = 8 A$	$T_{VJ} = 25^{\circ}C$		1.47	V
		$I_F = 16 A$			1.66	V
		$I_F = 8 A$	$T_{VJ} = 150^{\circ}C$		1.33	V
		$I_F = 16 A$			1.60	V
I_{FAV}	average forward current	$T_C = 115^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		8	A
V_{F0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.09	V
r_F	slope resistance				31	m Ω
R_{thJC}	thermal resistance junction to case				2.5	K/W
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		50	W
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		100	A
C_J	junction capacitance	$V_R = 400 V$ $f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		5	pF
I_{RM}	max. reverse recovery current	} $I_F = 8 A; V_R = 350 V$ $-di_F/dt = 100 A/\mu s$	$T_{VJ} = 25^{\circ}C$		2.5	A
			$T_{VJ} = 100^{\circ}C$		4	A
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}C$		60	ns
			$T_{VJ} = 100^{\circ}C$		100	ns



Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			20	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N



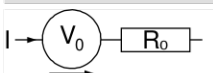
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEI8-06A	DSEI8-06A	Tube	50	434353

Similar Part	Package	Voltage class
DSEI8-06AS	TO-263AB (D2Pak) (2)	600
DFE10I600PM	TO-220ACFP (2)	600

Equivalent Circuits for Simulation

* on die level

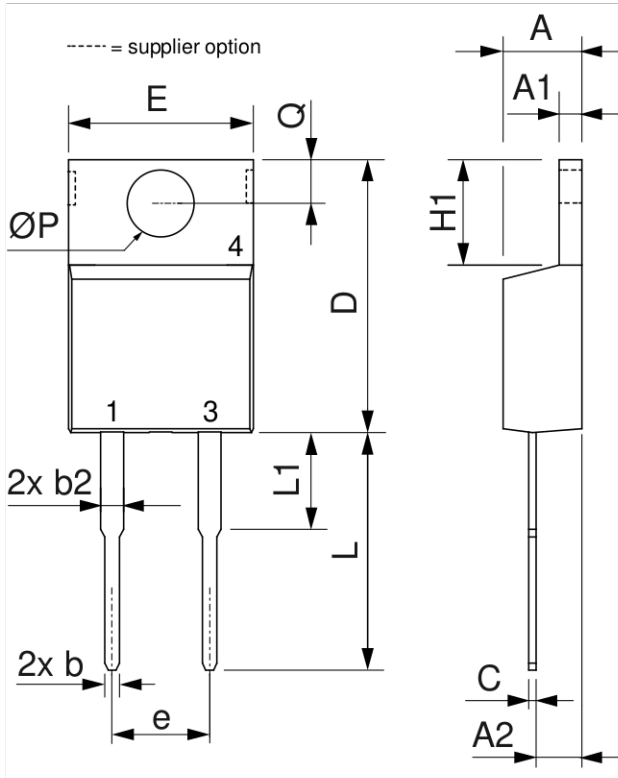
$T_{VJ} = 150^{\circ}C$



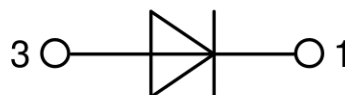
	Fast Diode	
$V_{0\ max}$	threshold voltage	1.09 V
$R_{0\ max}$	slope resistance *	28 mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125



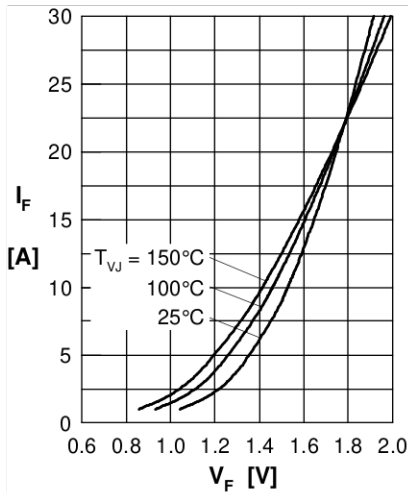
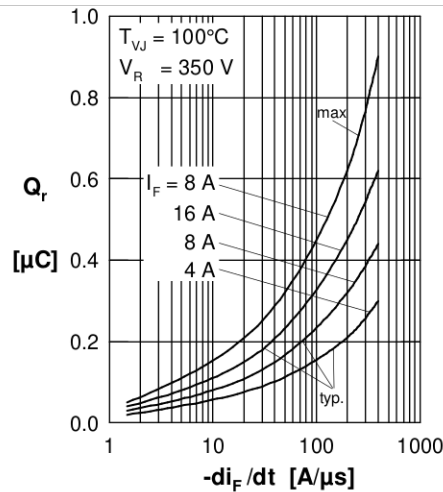
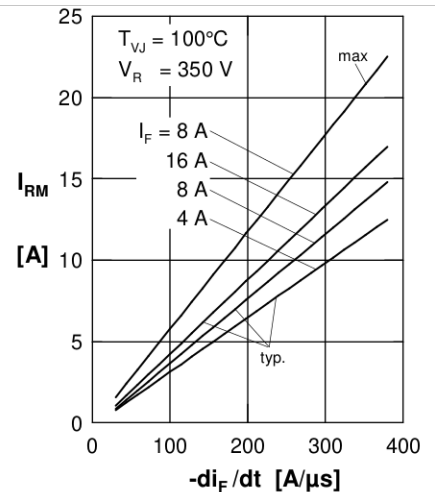
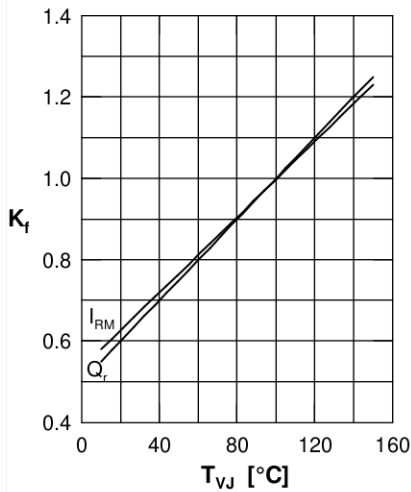
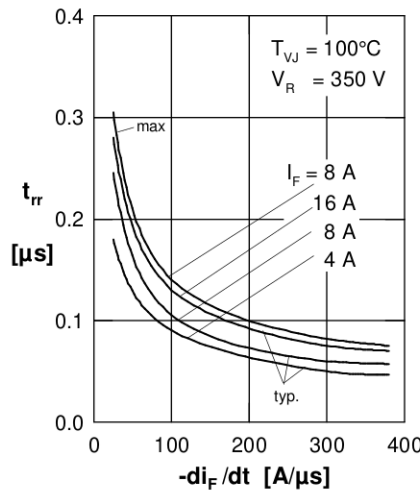
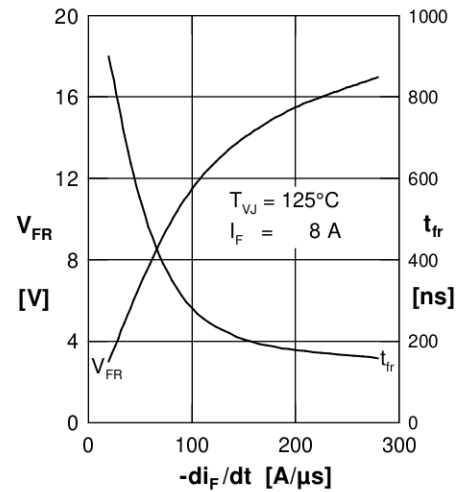
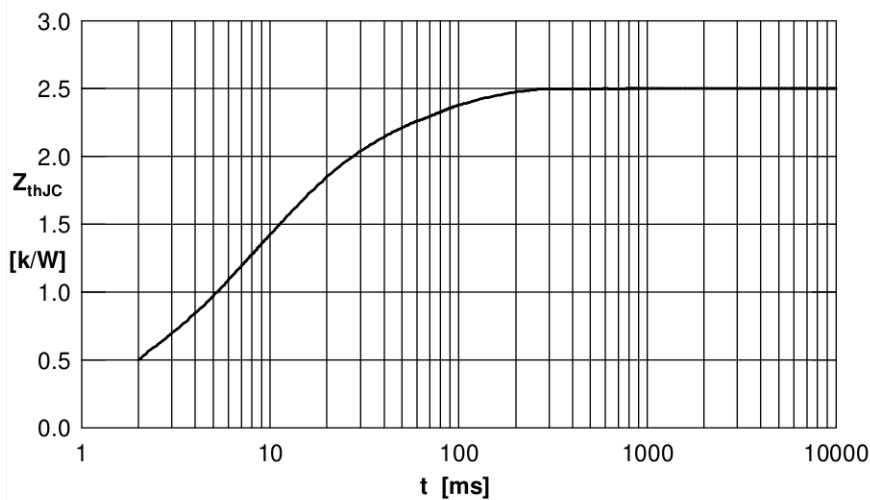
Fast Diode

 Fig. 1 Forward current I_F versus max. forward voltage drop V_F

 Fig. 2 Typ. reverse recov. charge Q_r versus $-di_F/dt$

 Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

 Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

 Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

 Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt


Fig. 7 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.100	0.001
2	0.020	0.010
3	0.450	0.003
4	0.640	0.060
5	1.380	0.010